

Description

The VS8NP04-S8 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

General Features

- N-Channel

$V_{DS} = 40V, I_D = 8A$

$R_{DS(ON)} < 19m\Omega @ V_{GS}=10V$

$R_{DS(ON)} < 29m\Omega @ V_{GS}=4.5V$

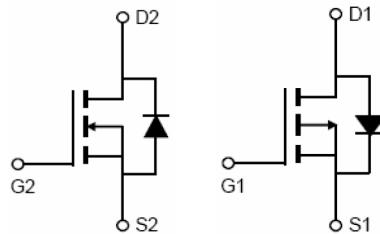
- P-Channel

$V_{DS} = -40V, I_D = -7A$

$R_{DS(ON)} < 35m\Omega @ V_{GS}=-10V$

$R_{DS(ON)} < 45m\Omega @ V_{GS}=-4.5V$

- High power and current handing capability
- Lead free product is acquired
- Surface mount package



N-channel

P-channel

Schematic diagram



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VS8NP04-S8	VS8NP04-S8	SOP-8	Ø330mm	12mm	

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	40	-40	V
Gate-Source Voltage		V_{GS}	± 20	± 20	V
Continuous Drain Current	$T_A=25^\circ C$	I_D	8	-7	A
	$T_A=70^\circ C$		6	-5.5	
Pulsed Drain Current ^(Note 1)		I_{DM}	40	-30	A
Maximum Power Dissipation	$T_A=25^\circ C$	P_D	2.0	2.0	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 To 150	-55 To 150	°C

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient ^(Note2)	R _{θJA}	N-Ch	62.5	°C/W
Thermal Resistance,Junction-to-Ambient ^(Note2)	R _{θJA}	P-Ch	62.5	°C/W

N-CH Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.5	2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =8A	-	14	19	mΩ
		V _{GS} =4.5V, I _D =4A	-	19	29	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =8A	33	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, F=1.0MHz	-	415	-	PF
Output Capacitance	C _{oss}		-	112	-	PF
Reverse Transfer Capacitance	C _{rss}		-	11	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, R _L =2.5Ω V _{GS} =10V, R _{GEN} =3Ω	-	4	-	nS
Turn-on Rise Time	t _r		-	3	-	nS
Turn-Off Delay Time	t _{d(off)}		-	15	-	nS
Turn-Off Fall Time	t _f		-	2	-	nS
Total Gate Charge	Q _g	V _{DS} =20V, I _D =8A, V _{GS} =10V	-	12	-	nC
Gate-Source Charge	Q _{gs}		-	3.2	-	nC
Gate-Drain Charge	Q _{gd}		-	3.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =8A	-	0.8	1.2	V

P-CH Electrical Characteristics ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-40V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics <small>(Note 3)</small>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.5	-2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-8A$	-	29	35	$m\Omega$
		$V_{GS}=-4.5V, I_D=-4A$	-	34	45	$m\Omega$
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-8A$	20	-	-	S
Dynamic Characteristics <small>(Note 4)</small>						
Input Capacitance	C_{iss}	$V_{DS}=-20V, V_{GS}=0V, F=1.0MHz$	-	520	-	PF
Output Capacitance	C_{oss}		-	100	-	PF
Reverse Transfer Capacitance	C_{rss}		-	65	-	PF
Switching Characteristics <small>(Note 4)</small>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-20V, R_L=2.3\Omega$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	7.5	-	nS
Turn-on Rise Time	t_r		-	5.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	19	-	nS
Turn-Off Fall Time	t_f		-	7	-	nS
Total Gate Charge	Q_g	$V_{DS}=-20V, I_D=-8A$ $V_{GS}=-10V$	-	13	-	nC
Gate-Source Charge	Q_{gs}		-	3.8	-	nC
Gate-Drain Charge	Q_{gd}		-	3.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <small>(Note 3)</small>	V_{SD}	$V_{GS}=0V, I_S=-10A$	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

N-Channel Typical Electrical and Thermal Characteristics (Curves)

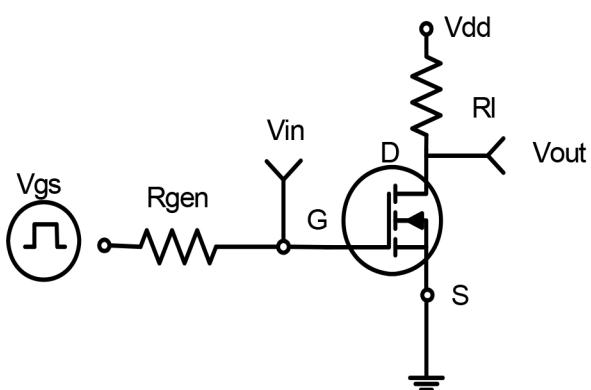


Figure 1:Switching Test Circuit

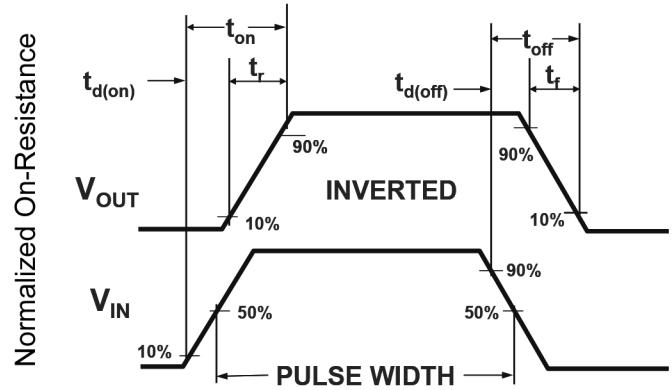


Figure 2:Switching Waveforms

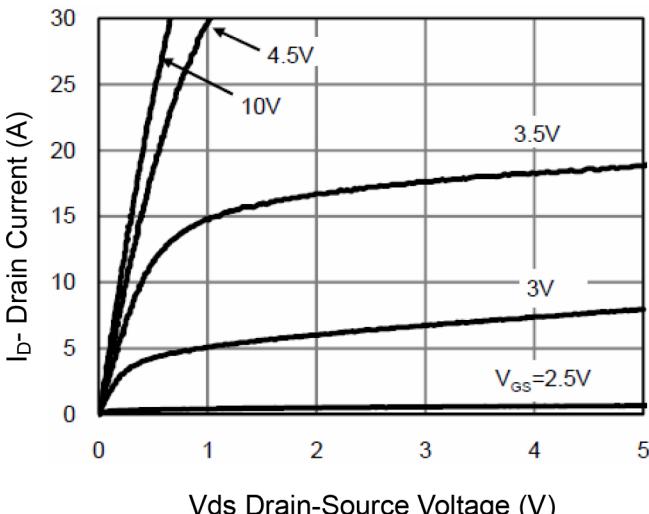


Figure 3 Output Characteristics

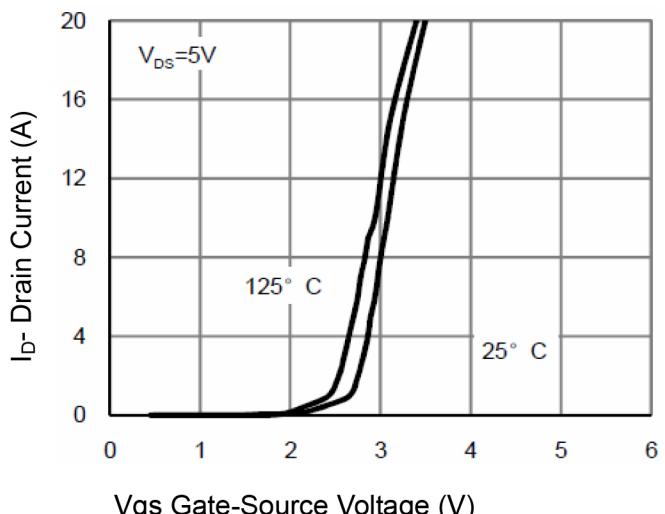


Figure 4 Transfer Characteristics

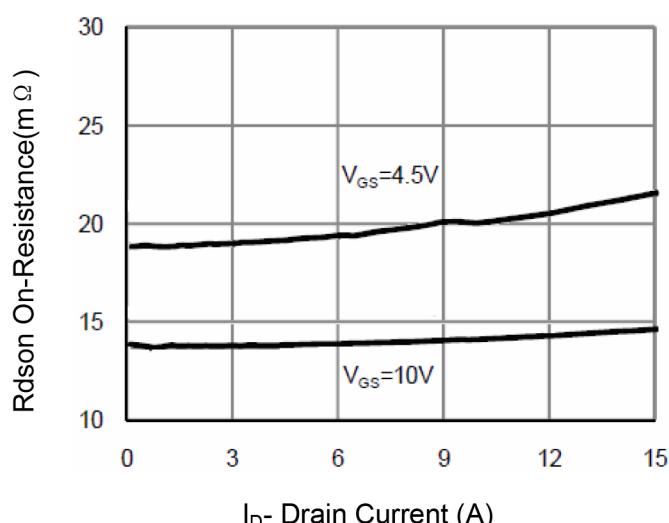


Figure 5 Drain-Source On-Resistance

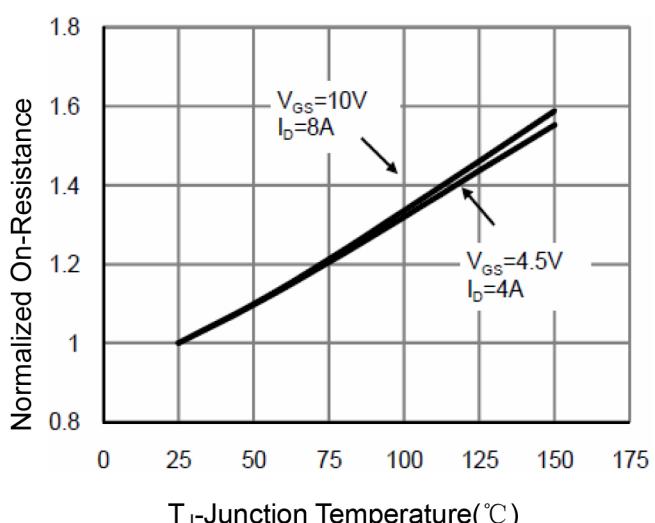


Figure 6 Drain-Source On-Resistance

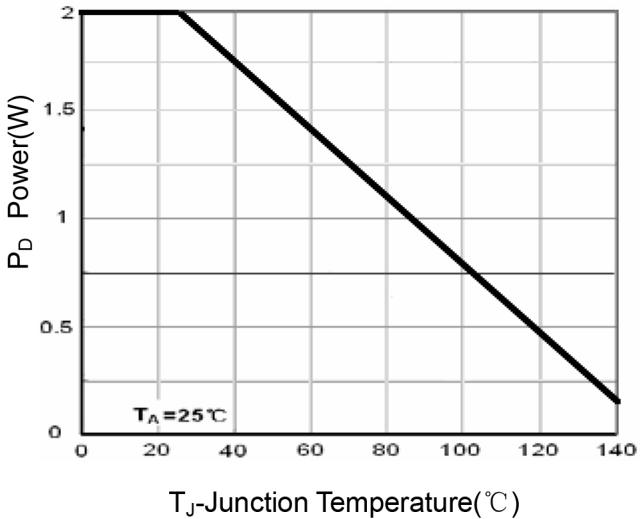
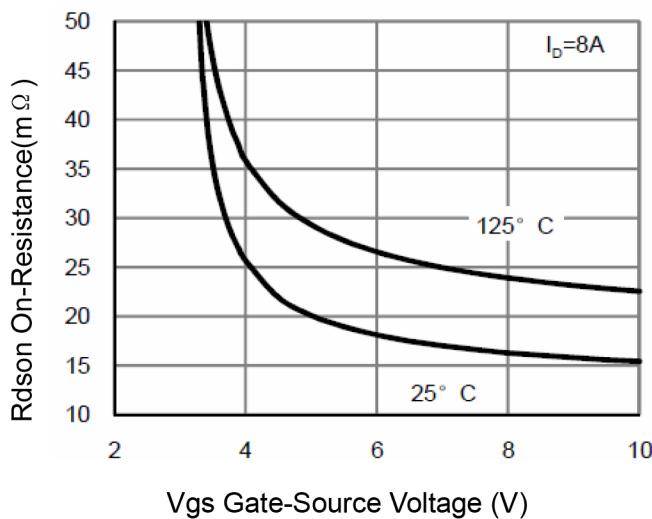


Figure 7 Rdson vs Vgs

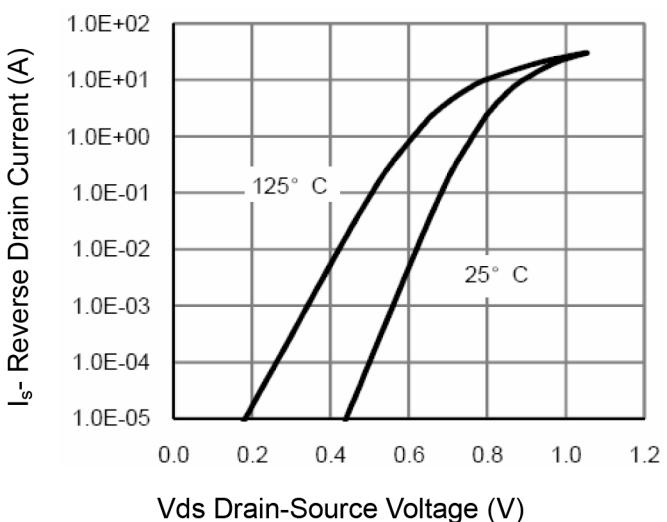


Figure 10 Source- Drain Diode Forward

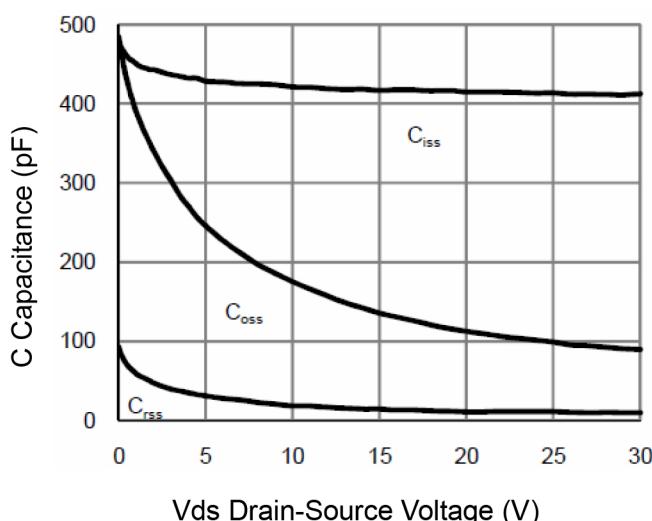


Figure 11 Capacitance vs Vds

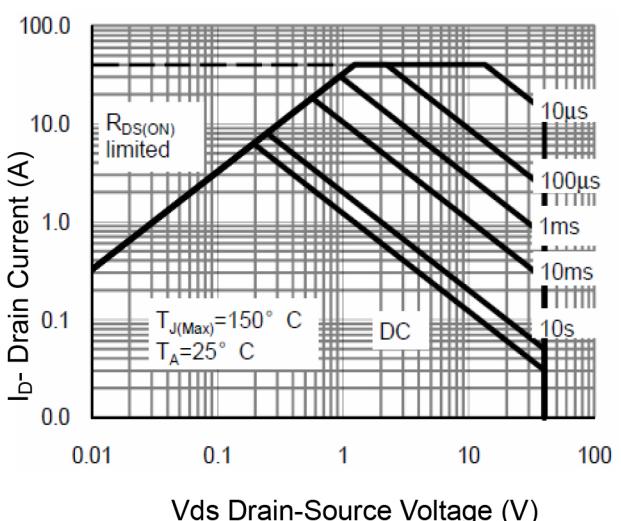


Figure 12 Safe Operation Area

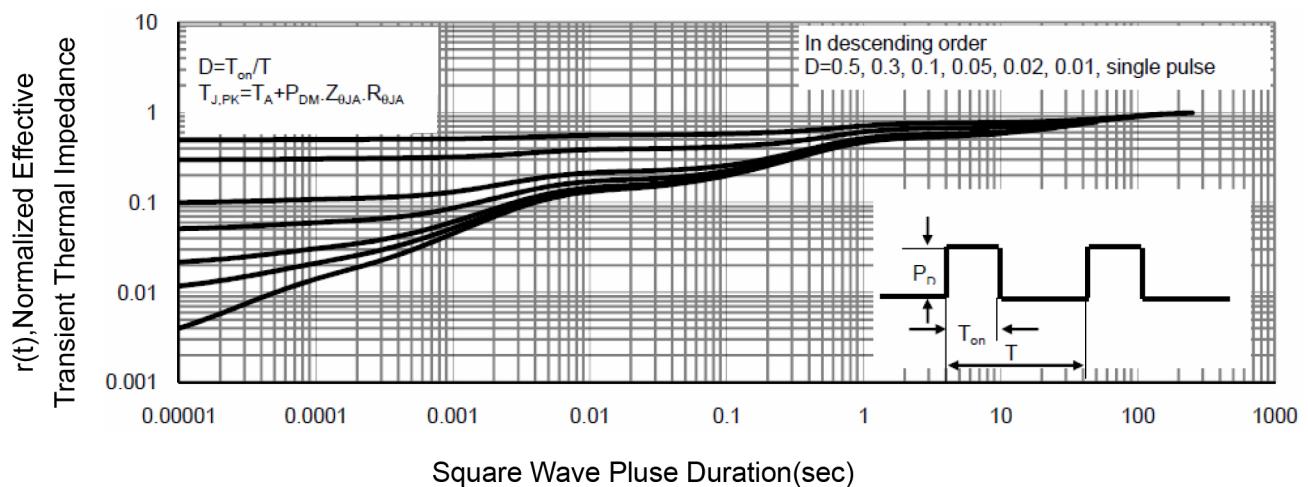


Figure 13 Normalized Maximum Transient Thermal Impedance

P- Channel Typical Electrical and Thermal Characteristics (Curves)

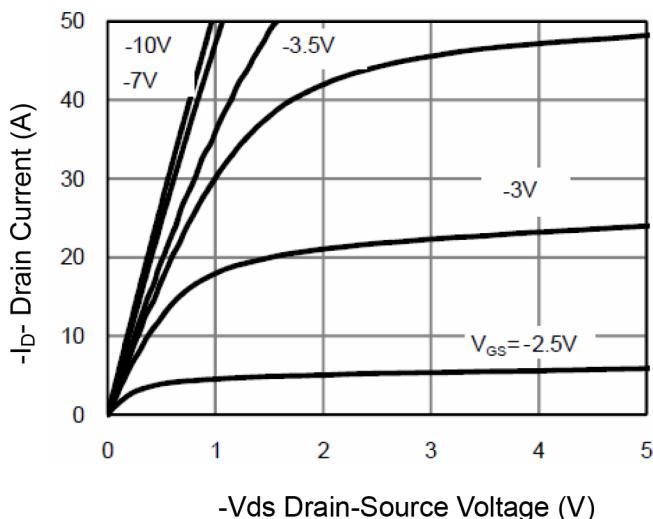


Figure 1 Output Characteristics

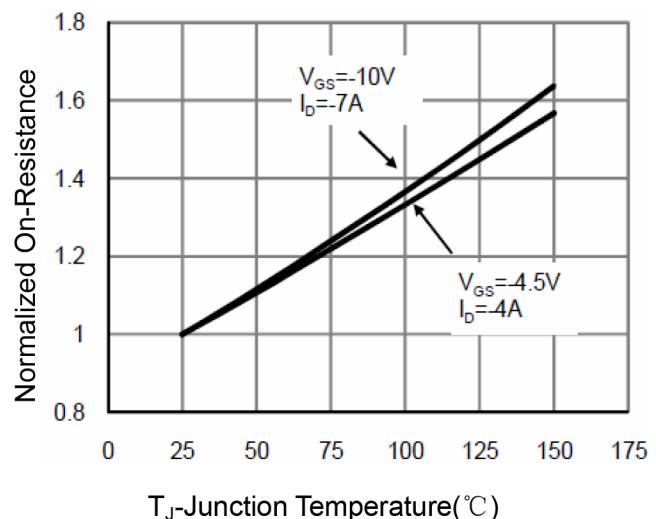


Figure 4 Rdson-Junction Temperature

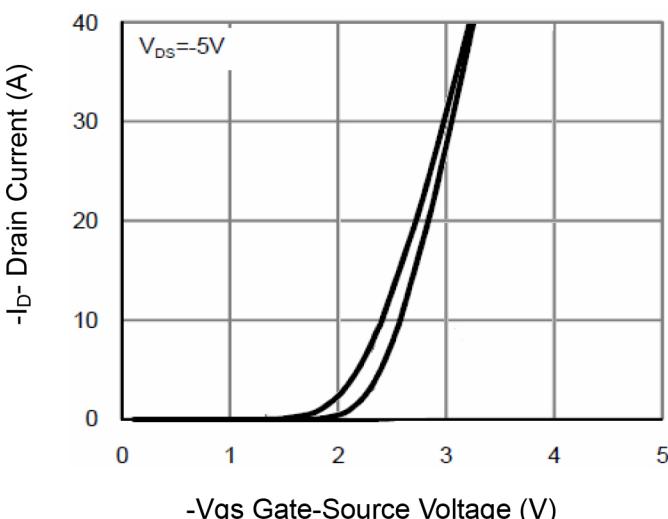


Figure 2 Transfer Characteristics

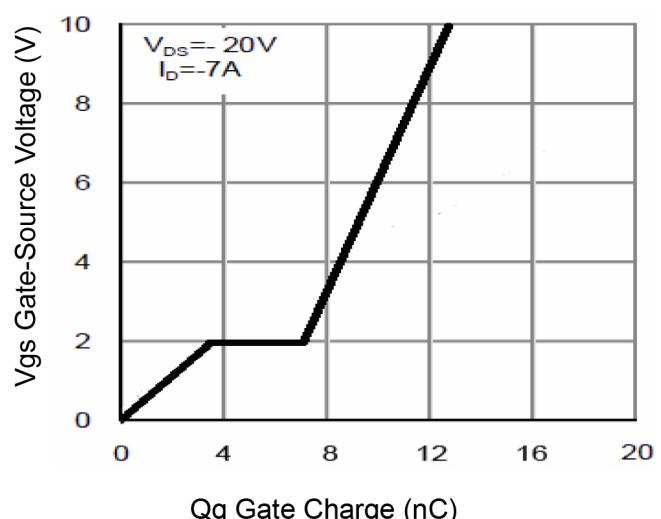


Figure 5 Gate Charge

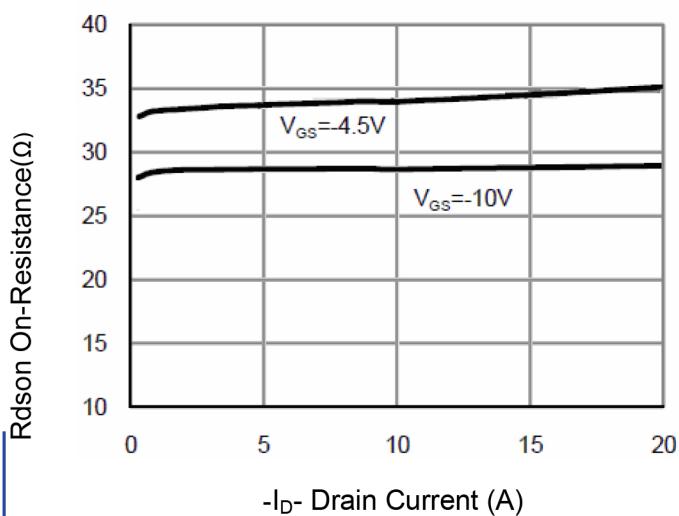


Figure 3 Rdson- Drain Current

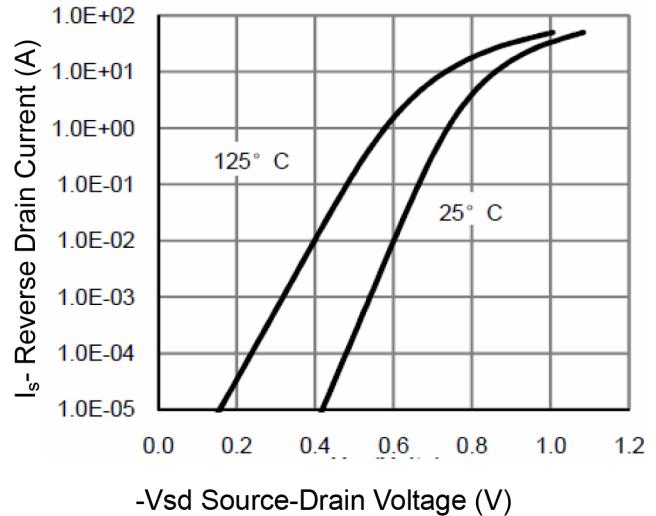
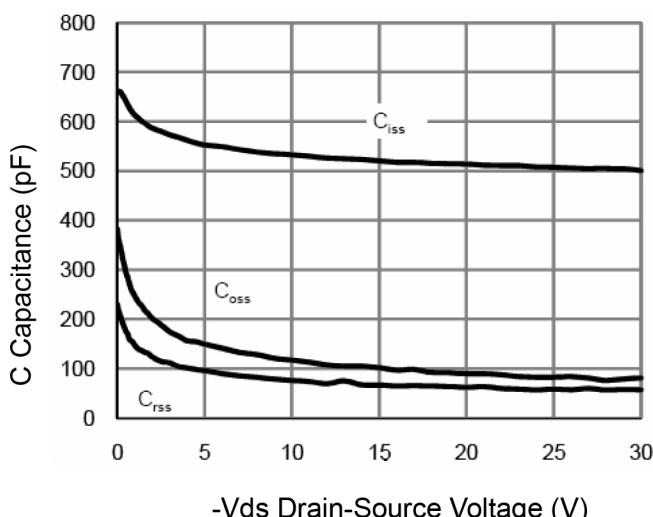
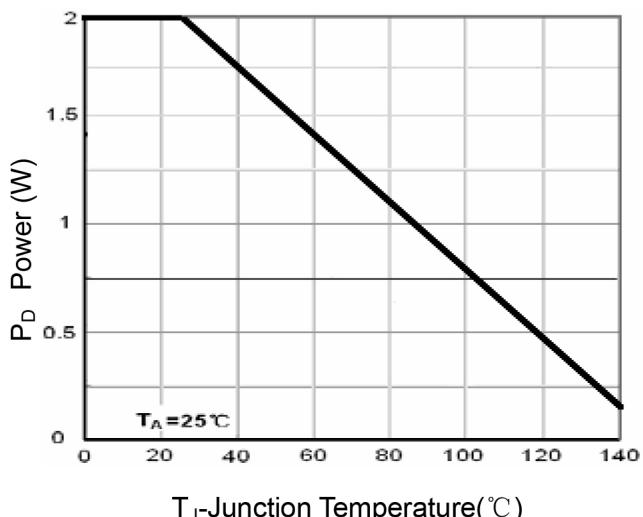
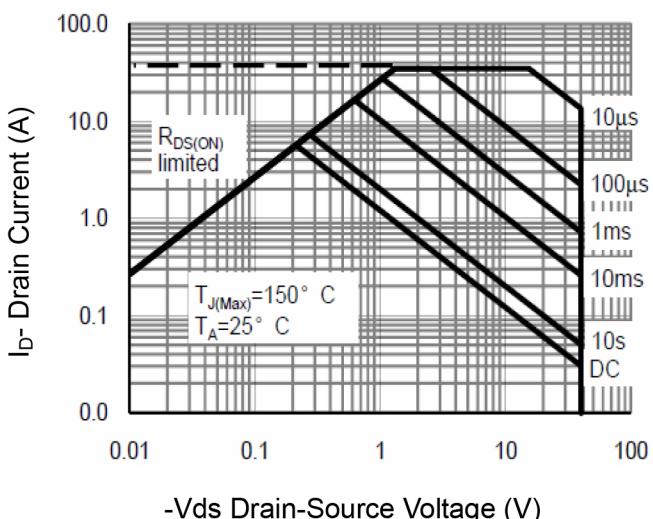
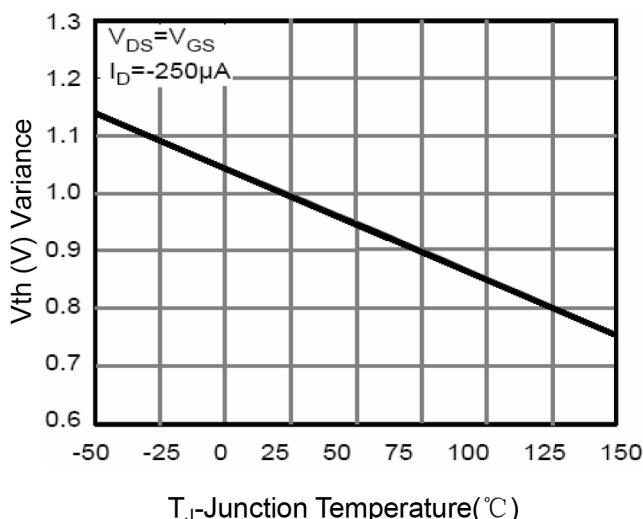
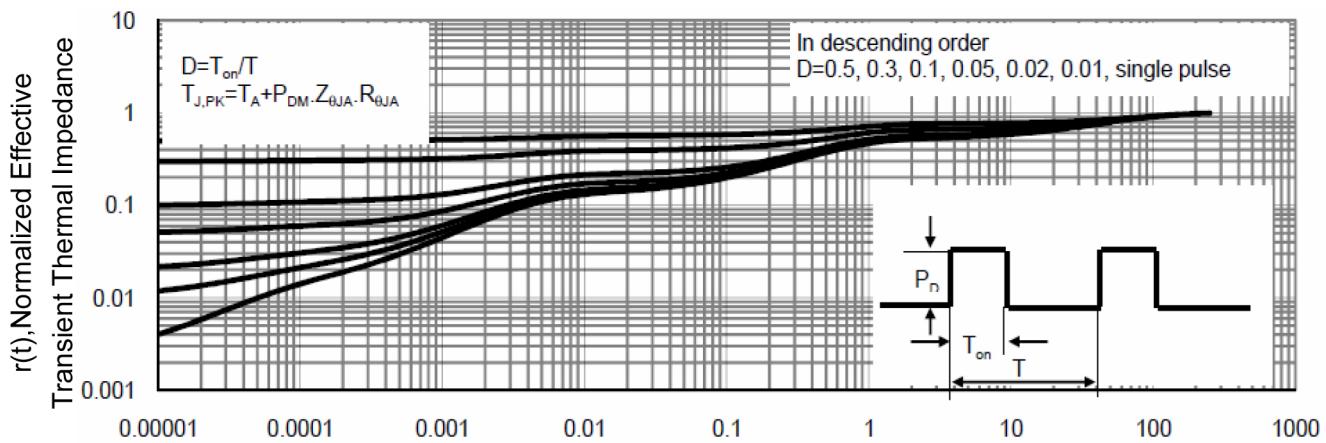


Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 Power Dissipation

Figure 8 Safe Operation Area

Figure 10 $V_{GS(\text{th})}$ vs Junction Temperature

Figure 11 Normalized Maximum Transient Thermal Impedance